

EAST: [10/29/99.wsp:1]

FileViewEditToolsWindowHelp

Active

L9: (3260) (257/377,382,384,388,412,413,486,754) (

L10: (253) 9 and metal near3 silicide with transistor

L12: (3757) 10 and (((silicon adj nitride) or SiN) with

L14: (1) 10 and ((silicon adj nitride) or SiN) and meta

Failed

(0) ((silicon adj nitride) or SiN) with (conformality wi

Saved

(2384) metal near3 silicide with transistor

(0) ((silicon adj nitride) or SiN) with (conformality wi

(0) (metal near3 silicide with transistor) and (((silicon

(32) ((silicon adj nitride) or SiN) with conformality

(3717) (((silicon adj nitride) or SiN) with conformalit

(1) (((silicon adj nitride) or SiN) with conformality) a

(24521) metal near3 silicide

(10) (metal near3 silicide) and (((silicon adj nitride) o

(1701) (257/640,649,760,900) CCLS.

DBs:USPAT,US-PG-PUB,EPQ,JPO,DERWENT,IBM,TDB

Default operator:OR

Plurals

Highlight all hit terms initially

	U	I	Document ID	Issue Date	Pages	Title	Current	Cur Re	Inventor	S	C	P	3	3
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20030022437 A1	20030130	23	Method of forming integr	438/245	438/	Fishburn, Fred	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
2	<input type="checkbox"/>	<input type="checkbox"/>	US 6475855 B1	20021105	22	Method of forming integr	438/239	438/	Fishburn, Fred	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6740559 B2	20040525	40	Semiconductor device co	438/303	438/	Higuchi, Toshihiko	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
4	<input type="checkbox"/>	<input type="checkbox"/>	US 6461951 B1	20021008	9	Method of forming a side	438/592	257/	Besser, Paul et al	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
5	<input type="checkbox"/>	<input type="checkbox"/>	US 6344677 B1	20020205	40	Semiconductor device co	257/408	257/	Higuchi, Toshihiko	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
6	<input type="checkbox"/>	<input type="checkbox"/>	US 6258646 B1	20010710	11	CMOS integrated circuit	438/231	257/	Fulford, Jr., H. Jim	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
7	<input type="checkbox"/>	<input type="checkbox"/>	US 6100142 A	20000808	10	Method of fabricating su	438/291	257/	Liao, Kuan-Yang	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
8	<input type="checkbox"/>	<input type="checkbox"/>	US 6144071 A	20001107	18	Ultrathin silicon nitride c	257/344	257/	Gardner, Mark I. et	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>

Ready

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